

AMENDMENTS TO THE CLAIMS

Claims 1-12 (cancelled)

Claim 13 (currently amended): A structure in an integrated circuit, the structure comprising:

 a last metal level; and
 a passivation level comprising a low-k dielectric substantially filling a space extending between a metal line and another metal line at least between metal lines in the last metal level.

Claim 14 (cancelled)

Claim 15 (original): The structure of claim 13 wherein the passivation level further comprises a layer of dielectric over the low-k dielectric and a topside material over the layer of dielectric.

Claim 16 (original): The structure of claim 13 wherein the low-k dielectric has a dielectric constant less than about 3.9.

Claim 17 (currently amended): The structure of claim 13 wherein the metal line has a thickness between about 8000 Angstroms and about 15000 Angstroms.

Claim 18 (currently amended): A structure in an integrated circuit, the structure comprising:

 means for carrying a signal in a last metal level; and
 means for reducing propagation delay of the signal, the means for reducing propagation delay of the signal comprising a low-k dielectric substantially filling a space between a metal line and an adjacent metal line in the last metal level.

Claim 19 (original): The structure of claim 18 wherein the means for carrying the signal comprises a metal line having a thickness between about 8000 Angstroms and about 15000 Angstroms.

Claim 20 (cancelled)

Claim 21 (new): The structure of claim 18 further comprising a layer of dielectric over the low-k dielectric and a topside material over the layer of dielectric.

Claim 22 (new): The structure of claim 18 wherein the low-k dielectric has a dielectric constant less than about 3.9.

Claim 23 (new) A structure in an integrated circuit, the structure comprising:

a plurality of metal lines over a first dielectric layer, the metal lines being in a last metal level; and

a low-k dielectric between metal lines in the plurality of metal lines, the low-k dielectric filling more than about 50% of a distance between a sidewall of a metal line and a sidewall of an adjacent metal line in the plurality of metal lines.

Claim 24 (new): The structure of claim 23 wherein the low-k dielectric has a dielectric constant less than about 3.9.

Claim 25 (new): The structure of claim 23 wherein the low-k dielectric is directly on the first dielectric layer.

Claim 26 (new): The structure of claim 23 further comprising a second dielectric layer over the low-k dielectric and a topside material over the second dielectric layer.